MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PIFD

MMBD7000LT1G-MS

Product specification





FEATURE

- Fast switching speed
- High Conductance

Applications

For general purpose switching

Reference News

SOT-23	Pin Configuration	MARKING
1. BASE 2. EMITTER 3. COLLECTOR	1 2	M5C

Absolute Maximum Ratings (Ta = 25 °C)

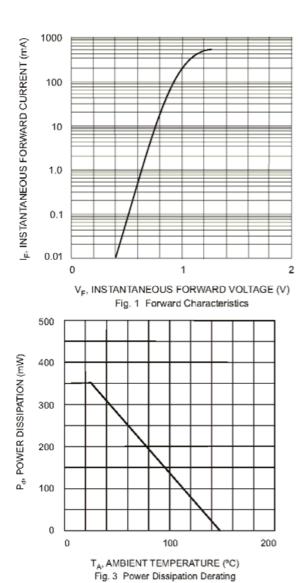
Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V_{RRM}	100	V
Reverse Voltage		V_R	100	V
Forward Current		lF	200	mA
,	at t = 1 s at t = 1 µs	I _{FSM}	1 2	А
Power Dissipation		P_d	350	mW
Junction and Storage Temperature Range		T_j , T_{stg}	- 65 to + 150	∘C

Characteristics at Ta = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at I _R = 100 μA	$V_{(BR)R}$	100	-	V
Forward Voltage at $I_F = 1$ mA at $I_F = 10$ mA at $I_F = 100$ mA at $I_F = 150$ mA	V _F	0.55 0.67 0.75	0.7 0.82 1.1 1.25	V
Reverse Current at $V_R = 50 \text{ V}$ at $V_R = 100 \text{ V}$ at $V_R = 50 \text{ V}$, $T_j = 125 ^{\circ}\text{C}$	I _R	- - -	1 3 100	μА
Total Capacitance at $V_R = 0 V$, $f = 1 MHz$	Ст	-	2	pF
Reverse Recovery Time at I_F = I_R = 10 mA, I_{rr} = 0.1 X I_R , R_L = 100 Ω	t _{rr}	-	4	ns



Typical Characteristics



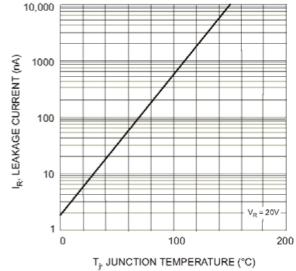
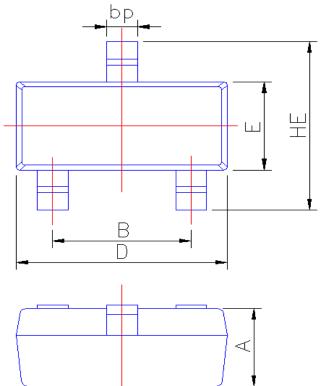
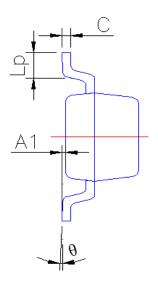


Fig. 2 Leakage Current vs Junction Temperature



PACKAGE MECHANICAL DATA







SOT-23

Sumb al	Dimension in Millimeters		
Symbol	Min	Max	
Α	0.90	1.10	
A1	0.013	0.100	
В	1.80	2.00	
bp	0.35	0.50	
С	0.09	0.150	
D	2.80	3.00	
E	1.20	1.40	
HE	2.20	2.80	
Lp	0.20	0.50	
θ	0°	5°	

REELSPECIFICATION

P/N	PKG	QTY
MMBD7000LT1G-MS	SOT-23	3000

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